

BC847CDXV6T1G, SBC847CDXV6T1G, BC847CDXV6T5G, BC848CDXV6T1G



ON Semiconductor®

<http://onsemi.com>

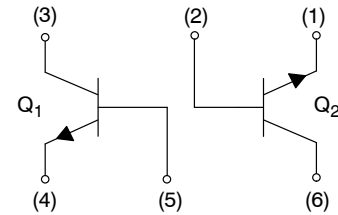
Dual General Purpose Transistors

NPN Duals

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-563 which is designed for low power surface mount applications.

Features

- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These are Pb-Free Devices



BC847CDXV6T1



SOT-563
CASE 463A

MAXIMUM RATINGS

| Rating | Symbol | BC847 | BC848 | Unit |
|--------------------------------|-----------|-------|-------|------------------|
| Collector - Emitter Voltage | V_{CEO} | 45 | 30 | V |
| Collector - Base Voltage | V_{CBO} | 50 | 30 | V |
| Emitter - Base Voltage | V_{EBO} | 6.0 | 5.0 | V |
| Collector Current - Continuous | I_C | 100 | 100 | mA _{dc} |

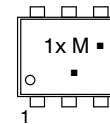
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

| Characteristic (One Junction Heated) | Symbol | Max | Unit |
|---|-----------------|-------------|----------------------------|
| Total Device Dissipation, (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D | 357 2.9 | mW mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction-to-Ambient (Note 1) | $R_{\theta JA}$ | 350 | $^\circ\text{C}/\text{W}$ |
| Characteristic (Both Junctions Heated) | Symbol | Max | Unit |
| Total Device Dissipation, (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D | 500 4.0 | mW mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction-to-Ambient (Note 1) | $R_{\theta JA}$ | 250 | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature Range | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |

1. FR-4 @ Minimum Pad

MARKING DIAGRAMS



- 1x = Device Code
x = G or M
M = Date Code
■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

BC847CDXV6T1G, SBC847CDXV6T1G, BC847CDXV6T5G, BC848CDXV6T1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit | |
|--|--|----------------------|------------|--------|-----------|----------|
| OFF CHARACTERISTICS | | | | | | |
| Collector–Emitter Breakdown Voltage (I _C = 10 mA) | BC847CDXV6T1, SBC847CDXV6 BC848CDXV6T1 | V _{(BR)CEO} | 45 30 | – – | – – | V |
| Collector–Emitter Breakdown Voltage (I _C = 10 μA, V _{EB} = 0) | BC847CDXV6T1, SBC847CDXV6 BC848CDXV6T1 | V _{(BR)CES} | 50 30 | – – | – – | V |
| Collector–Base Breakdown Voltage (I _C = 10 μA) | BC847CDXV6T1, SBC847CDXV6 BC848CDXV6T1 | V _{(BR)CBO} | 50 30 | – – | – – | V |
| Emitter–Base Breakdown Voltage (I _E = 1.0 μA) | BC847CDXV6T1, SBC847CDXV6 BC848CDXV6T1 | V _{(BR)EBO} | 6.0 5.0 | – – | – – | V |
| Collector Cutoff Current (V _{CB} = 30 V) | (V _{CB} = 30 V, T _A = 150°C) | I _{CBO} | – – | – – | 15 5.0 | nA μA |

ON CHARACTERISTICS

| | | | | | | |
|--|--|----------------------|----------|------------|-------------|----|
| DC Current Gain (I _C = 10 μA, V _{CE} = 5.0 V) (I _C = 2.0 mA, V _{CE} = 5.0 V) | | h _{FE} | – 420 | 270 520 | – 800 | – |
| Collector–Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA) (I _C = 100 mA, I _B = 5.0 mA) | | V _{CE(sat)} | – – | – – | 0.25 0.6 | V |
| Base–Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA) (I _C = 100 mA, I _B = 5.0 mA) | | V _{BE(sat)} | – – | 0.7 0.9 | – – | V |
| Base–Emitter Voltage (I _C = 2.0 mA, V _{CE} = 5.0 V) (I _C = 10 mA, V _{CE} = 5.0 V) | | V _{BE(on)} | 580 – | 660 – | 700 770 | mV |

SMALL-SIGNAL CHARACTERISTICS

| | | | | | | |
|---|--|------------------|-----|---|-----|-----|
| Current–Gain – Bandwidth Product (I _C = 10 mA, V _{CE} = 5.0 Vdc, f = 100 MHz) | | f _T | 100 | – | – | MHz |
| Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz) | | C _{obo} | – | – | 1.5 | pF |
| Noise Figure (I _C = 0.2 mA, V _{CE} = 5.0 Vdc, R _S = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz) | | NF | – | – | 10 | dB |

ORDERING INFORMATION

| Device | Specific Marking | Package | Shipping [†] |
|----------------|------------------|----------------------|--------------------------|
| BC847CDXV6T1G | 1G | SOT–563 (Pb–Free) | 4000 Units / Tape & Reel |
| SBC847CDXV6T1G | | | 8000 Units / Tape & Reel |
| BC847CDXV6T5G | | | |
| BC848CDXV6T1G | 1L | SOT–563 (Pb–Free) | 4000 Units / Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

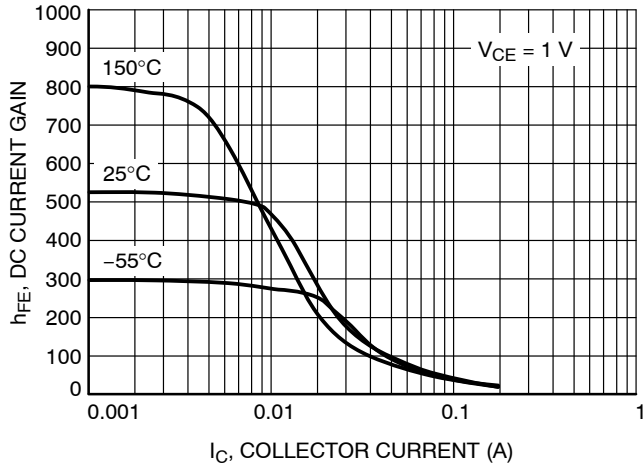


Figure 1. DC Current Gain vs. Collector Current

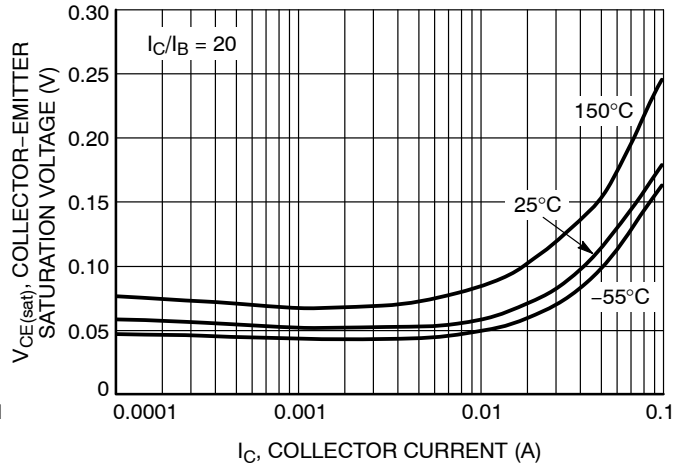


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

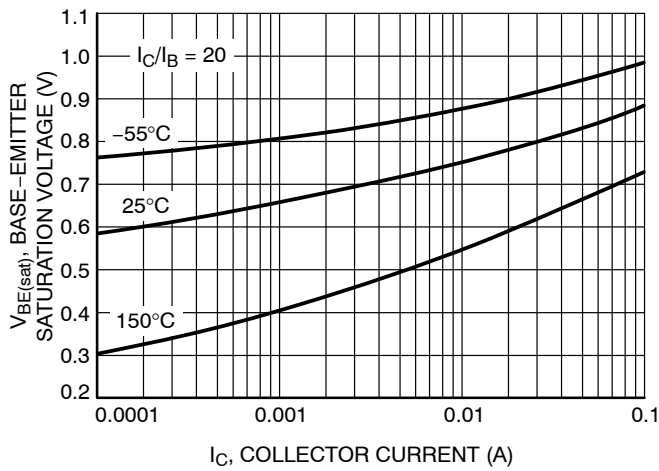


Figure 3. Base Emitter Saturation Voltage vs. Collector Current

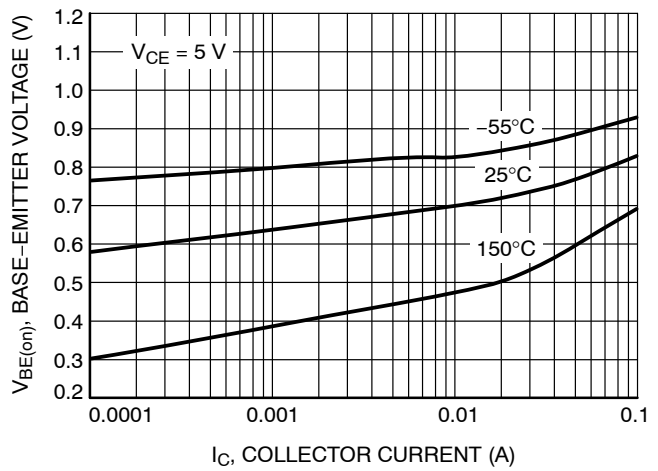


Figure 4. Base Emitter Voltage vs. Collector Current

TYPICAL CHARACTERISTICS

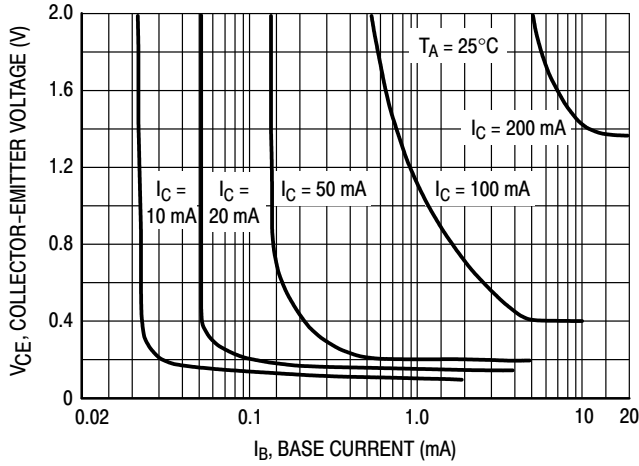


Figure 5. Collector Saturation Region

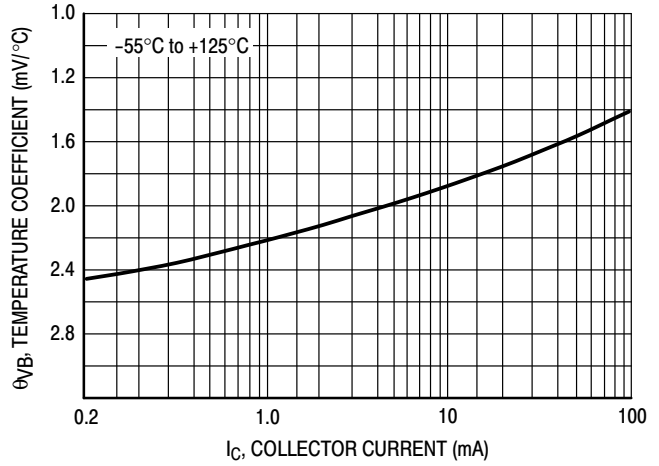


Figure 6. Base-Emitter Temperature Coefficient

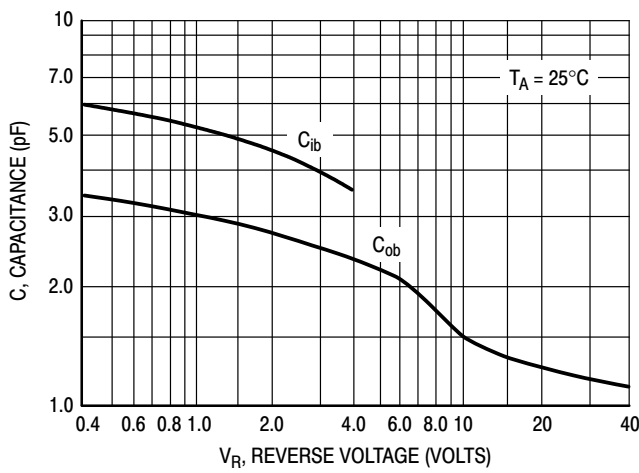


Figure 7. Capacitances

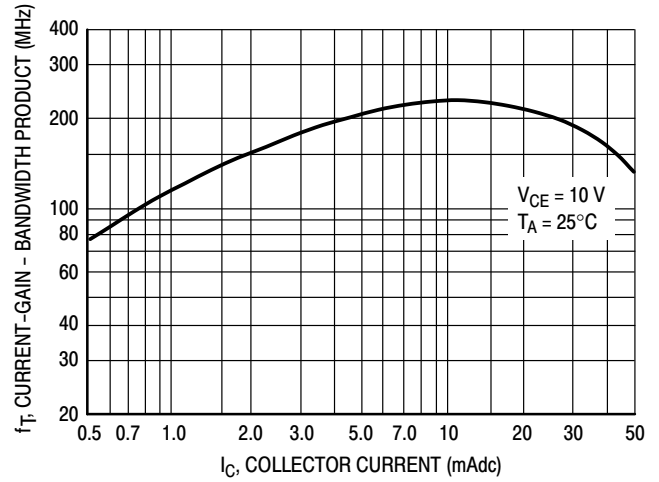


Figure 8. Current-Gain - Bandwidth Product

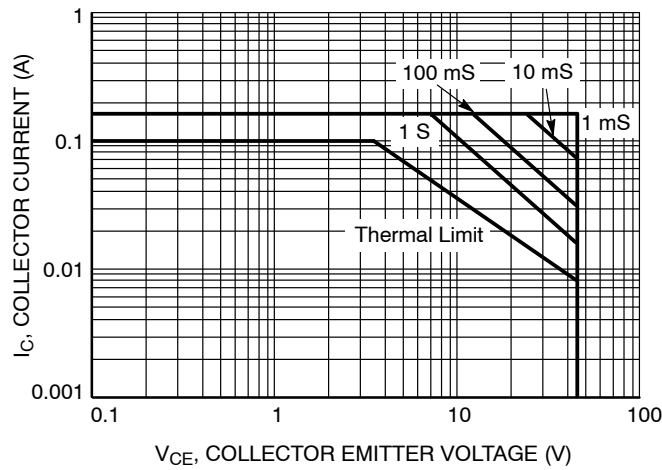


Figure 9. Safe Operating Area

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

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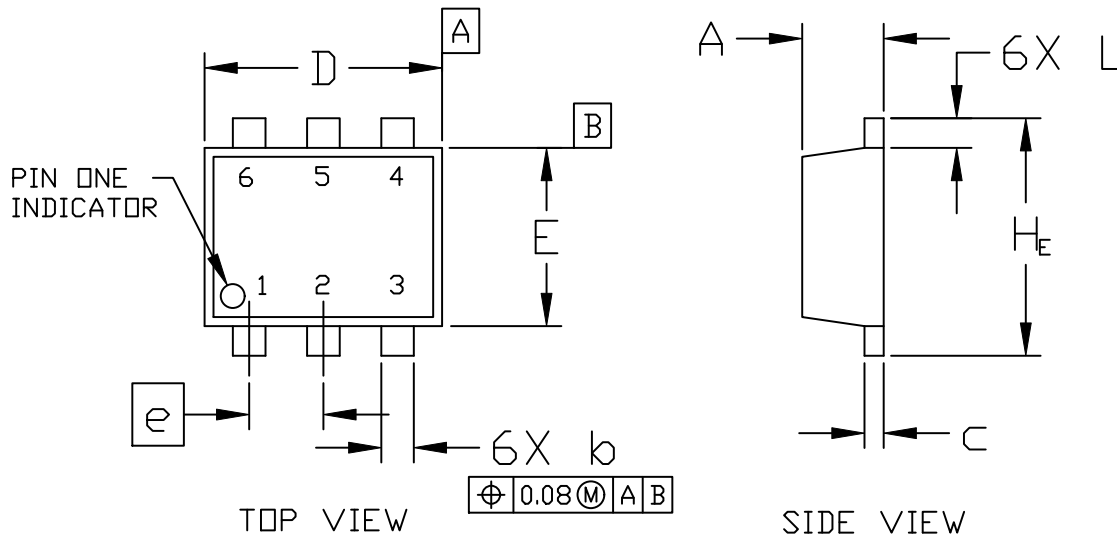
SCALE 4:1

SOT-563, 6 LEAD
CASE 463A
ISSUE H

DATE 26 JAN 2021

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.



| DIM | MILLIMETERS | | |
|----------------|-------------|------|------|
| | MIN. | NOM. | MAX. |
| A | 0.50 | 0.55 | 0.60 |
| b | 0.17 | 0.22 | 0.27 |
| c | 0.08 | 0.13 | 0.18 |
| D | 1.50 | 1.60 | 1.70 |
| E | 1.10 | 1.20 | 1.30 |
| e | 0.50 BSC | | |
| L | 0.10 | 0.20 | 0.30 |
| H _E | 1.50 | 1.60 | 1.70 |

RECOMMENDED MOUNTING FOOTPRINT*

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

| | | |
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SOT-563, 6 LEAD
CASE 463A
ISSUE H

DATE 26 JAN 2021

STYLE 1:
PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1

STYLE 2:
PIN 1. EMITTER 1
2. EMITTER 2
3. BASE 2
4. COLLECTOR 2
5. BASE 1
6. COLLECTOR 1

STYLE 3:
PIN 1. CATHODE 1
2. CATHODE 1
3. ANODE/ANODE 2
4. CATHODE 2
5. CATHODE 2
6. ANODE/ANODE 1

STYLE 4:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

STYLE 5:
PIN 1. CATHODE
2. CATHODE
3. ANODE
4. ANODE
5. CATHODE
6. CATHODE

STYLE 6:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE

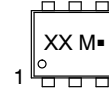
STYLE 8:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

STYLE 9:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

STYLE 10:
PIN 1. CATHODE 1
2. N/C
3. CATHODE 2
4. ANODE 2
5. N/C
6. ANODE 1

STYLE 11:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

**GENERIC
MARKING DIAGRAM***



XX = Specific Device Code
M = Month Code
■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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